

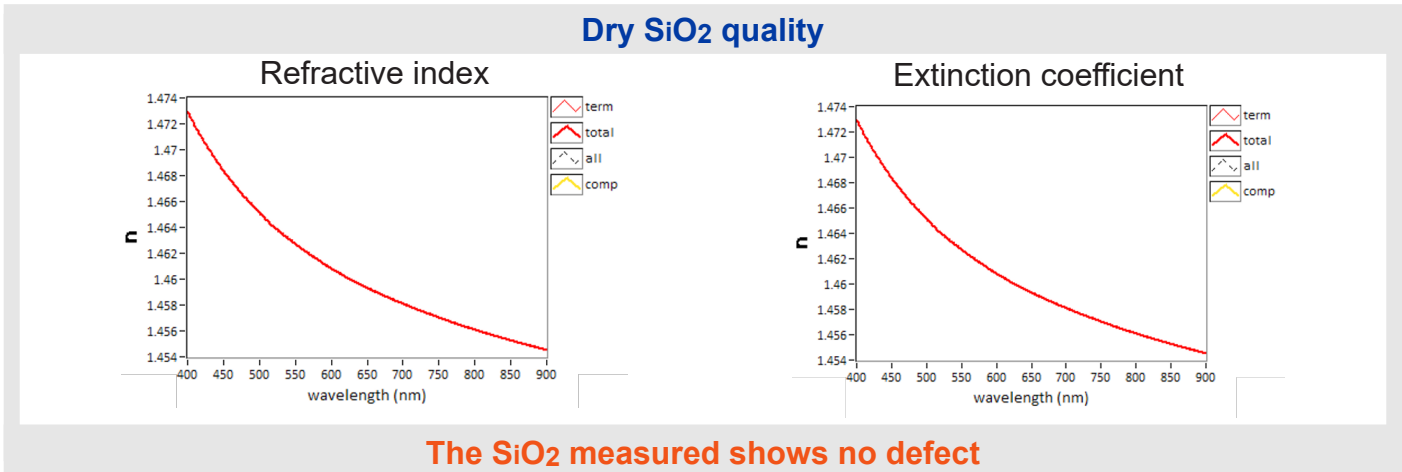
# Thin film Layers



- Totally customized
- Dry oxidation
- Breakdown voltage:  
>200 V for 285 nm thick  
layer
- Low Roughness  
( $< 3 \text{ \AA RMS}$ )
- Any metallic layers
- Multilayers deposition



Oxidation & Deposition on Silicon	Thickness (nm)	Thickness tolerances (µm)	Diameters
<b>Oxidation</b>			
Wet oxidation	200 - 3000	± 3%	From 1" to 6"
High purity dry oxidation	20 - 300	± 5%	From 1" to 6"
<b>Option</b>			
Single face oxidation			



Single layer deposition / metallization				
Silicon nitride	LPCVD	20 - 500	± 5% Option: Low Stress	From 2" to 4"
	PECVD			
Oxide nitride	PECVD	20 - 500	± 5%	From 2" to 4"
Polysilicon	LPCVD	20 - 600	± 8%	From 2" to 4"
Cr, Ti, Au, Al, Pt, Mo, W Highly reflective silver coating	PVD sputtering	20 -1000	± 10%	From 1" to 6" depending on metals
Ni, Cu, Ir, Ta, Al <sub>2</sub> O <sub>3</sub>	Evaporation			
Cr/Au TiW with Ti : 10% W: 90% TiW /Au with Ti : 10% W: 90% Ti/Pt	PVD			

Multilayers deposition
On request

